

64Mx32 NOR Flash Multi-Chip Package 3.0V Page Mode Flash Memory

W764M32V-XSBX



Not Recommended for New Designs — Replaced by W764M32V1-XBX

FEATURES

- Single power supply operation
 - 3 volt read, erase, and program operations
- I/O Control
 - All input levels (address, control, and DQ input levels) and outputs are determined by voltage on V_{IO} input. V_{IO} range is 1.65 to V_{CC}
- Secured Silicon Sector region
 - 128-word/256-byte sector for permanent, secure identification through an 8-word/16-byte random Electronic Serial Number, accessible through a command sequence
 - May be programmed and locked at the factory or by the customer
- Flexible sector architecture
 - Five hundred twelve 64 Kword (128 Kbyte) sectors
 - Two hundred fifty-six 64 Kword (128 Kbyte) sectors
 - One hundred twenty-eight 64 Kword (128 Kbyte) sectors
- Compatibility with JEDEC standard
 - Provides software compatibility for single-power supply flash, and superior inadvertent write protection
- 100,000 erase cycles per sector typical
- 20-year data retention typical

PERFORMANCE CHARACTERISTICS

- High Performance
 - 100, 120 ns
 - 8-word/16-byte page read buffer
 - 25 ns page read times
 - 16-word/32-byte write buffer reduces overall programming time for multiple-word updates
- Package option
 - 107 BGA, 14mm x 17mm
 - 1.0mm pitch
- Software features
 - Program Suspend and Resume: read other sectors before programming operation is completed
 - Erase Suspend and Resume: read/program other sectors before an erase operation is completed
 - Data# polling and toggle bits provide status
 - Unlock Bypass Program command reduces overall multiple-word programming time
 - CFI (Common Flash Interface) compliant: allows host system to identify and accommodate multiple flash devices

- Hardware features
 - Advanced Sector Protection
 - WP#/ACC input accelerates programming time (when high voltage is applied) for greater throughput during system production. Protects first or last sector regardless of sector protection settings
 - Hardware reset input (RESET#) resets device
 - Ready/Busy# output (RY/BY#) detects program or erase cycle completion

* This product is subject to change without notice.

GENERAL DESCRIPTION

The W764MB2V-XSBX device is a 3.0V single power flash memory. The device utilizes four organized as 33,554,432 words or 67, 108,864 bytes. The device has a 32-bit wide data bus, can be programmed either in the host system or in standard EPROM programmers.

Each device requires a single 3.0 volt power supply for both read and write functions. In addition to a V_{CC} input, a high-voltage accelerated program (WP# / ACC) input provides shorter programming times through increased current. This feature is intended to facilitate factory throughput during system production, but may also be used in the field if desired.

The devices are entirely command set compatible with the JEDEC single power-supply Flash standard. Commands are written to the device using standard microprocessor write timing. Write cycles also internally latch addresses and data needed for the programming and erase operations.

The sector erase architecture allows memory sectors to be erased and reprogrammed without affecting the data contents of other sectors. The device is fully erased when shipped from the factory.

Device programming and erasure are initiated through command sequences. Once a program or erase operation has begun, the host system need only poll the DQ7 (Data# Polling) or DQ6 (toggle) status bits or monitor the Ready / Busy# (RY / BY#) output to determine whether the operation is complete. To facilitate programming, an Unlock Bypass mode reduces command sequence overhead by requiring only two write cycles to program data instead of four.

The I/O (V_{IO}) control allows the host system to set the voltage levels that the device generates and tolerates on all input levels (address, chip control, and DQ input levels) to the same voltage level that is asserted on the V_{IO} pin. This allows the device to operate in a 1.8 V or 3 V system environment as required.

Hardware data protection measures include a low V_{CC} detector that automatically inhibits write operations during power transitions.

Persistent Sector Protection provides in-system, command-enabled protection of any combination of sectors using a single power supply at V_{CC}. Password Sector Protection prevents unauthorized write and erase operations in any combination of sectors through a user-defined 64-bit password.

The erase Suspend / Erase Resume feature allows the host system to pause and erase operation in a given sector to read or program any other sector and then complete the erase operation. The Program Suspend / Program Resume feature enables the host system to pause the program operation in a given sector to read any other sector and then complete the program operation.

The hardware RESET# pin terminates any operation in progress and resets the device, after which it is then ready for a new operation. The RESET# pin may be tied to the system reset circuitry. A system reset would thus also reset the device, enabling

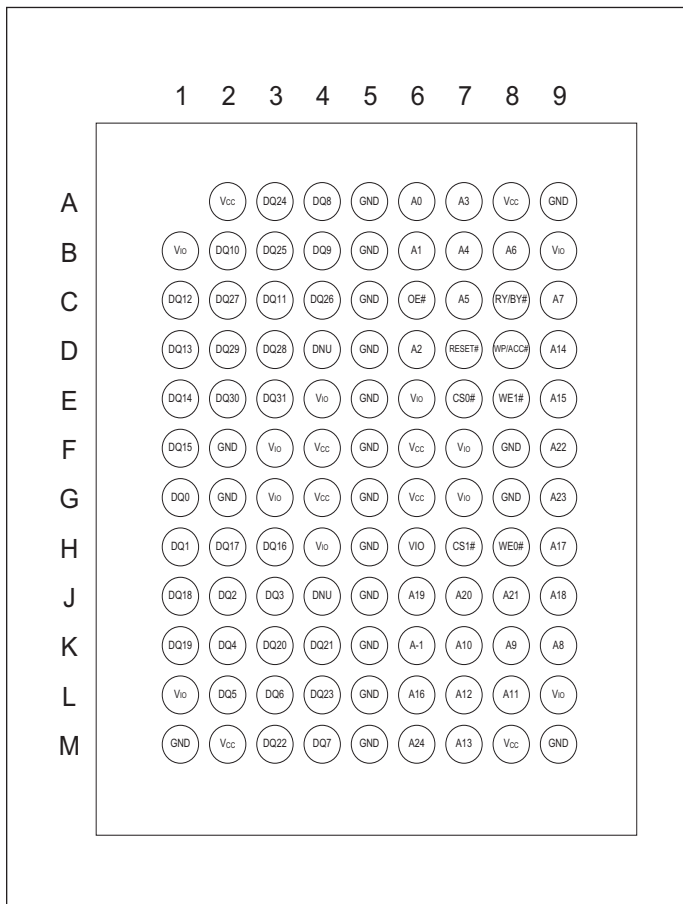
the host system to read boot-up firmware from the Flash memory device.

The device reduces power consumption in the standby mode when it detects specific voltage levels on CS# and RESET#, or when addresses have been stable for a specified period of time.

The Secured Silicon Sector provides a 128-work/256-byte area for code or data that can be permanently protected. Once this sector is protected, no further changes within the sector can occur.

The Write Protect (WP# / ACC) feature protects the first or last sector by asserting a logic low on the WP# pin.

FIGURE 1 – PIN CONFIGURATION (TOP VIEW)

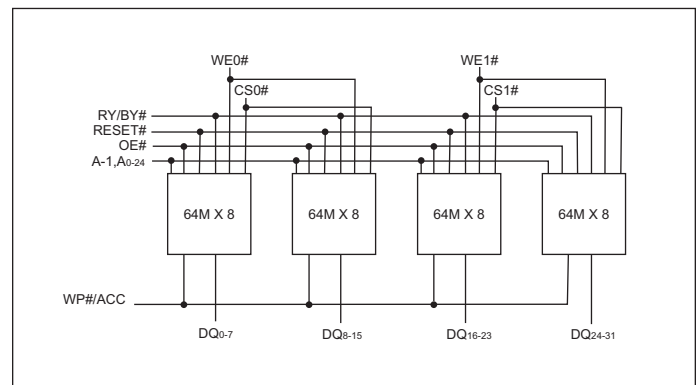


PIN DESCRIPTION

DQ ₀₋₃₁	Data Inputs/Outputs
A _{0-24, A-1*}	Address Inputs
WE# ₀₋₁	Write Enables
CS# ₀₋₁	Chip Selects
OE#	Output Enable
RESET#	Hardware Reset
WP#/ACC	Hardware Write Protection/Acceleration
RY/BY#	Ready/Busy Output
V _{CC}	Power Supply
V _{IO}	I/O Power Supply
GND	Ground
DNU	Do Not Use

* A-1 is the least significant address.

BLOCK DIAGRAM



ABSOLUTE MAXIMUM RATINGS

Parameter		Unit
Operating Temperature	-55 to +125	°C
Supply Voltage Range (V _{cc})	-0.5 to +4.0	V
Signal Voltage Range	-0.5 to V _{cc} +0.5	V
Storage Temperature Range	-55 to +125	°C

NOTES:

1. Minimum DC voltage on input or input or I/Os is -0.5V. During voltage transitions, inputs or I/Os may overshoot V_{SS} to -2.0V for periods of up to 20ns. Maximum DC voltage on input or I/Os is V_{CC} + 0.5V. During voltage transitions, input or I/O pins may overshoot to V_{CC} + 2.0V for periods up to 20ns
2. Minimum DC input voltage on pins A9, OE#, and ACC is 0.5V. During voltage transitions, A9, OE#, and ACC may overshoot V_{SS} to -2.0V for periods of up to 20ns. Maximum DC input voltage on pin A9, OE#, and ACC is +12.5V which may overshoot to +14.0V for periods up to 20ns
3. No more than one output may be shorted to ground at a time. Duration of the short circuit should not be greater than one second.
4. Stresses above those listed under Absolute Maximum Ratings may cause permanent damage to the device. This is a stress rating only; functional operation of the device at these or any other conditions above those indicated in the operational sections of the data sheet is not implied. Exposure of the device to absolute maximum rating conditions for extended periods may affect device reliability

RECOMMENDED OPERATING CONDITIONS

Parameter	Symbol	Min	Max	Unit
Supply Voltage	V _{CC}	3.0	3.6	V
Operating Temp. (Mil.)	T _A	-55	+125	°C
Operating Temp. (Ind.)	T _A	-40	+85	°C

BGA THERMAL RESISTANCE

Description	Symbol	Typical	Units	Notes
Junction to Ambient (No Airflow)	Theta JA	22.1	°C/W	
Junction to Ball	Theta JB	22.1	°C/W	
Junction to Case (Top)	Theta JC	12.0	°C/W	

CAPACITANCET_A = +25°C, F = 1.0MHz

Parameter	Symbol	Max	Unit
WE#0-1 capacitance	C _{WE}	14	pF
CS#0-1 capacitance	C _{CS}	20	pF
Data I/O capacitance	C _{I/O}	10	pF
Address input capacitance	C _{AD}	28	pF
RESET# capacitance	C _{RS}	80	pF
WP#/ACC capacitance	C _{RB}	116	pF
OE# capacitance	C _{OE}	23	pF

This parameter is guaranteed by design but not tested.

DATA RETENTION

Parameter	Test Conditions	Min	Unit
Pattern Data Retention Time	150°C	10	Years
	125°C	20	Years

DC CHARACTERISTICS – CMOS COMPATIBLE

$$V_{CC} = 3.3V \pm 0.3V, -55^{\circ}C \leq T_A \leq +125^{\circ}C$$

Parameter	Symbol	Conditions	Min	Typ	Max	Unit
Input Load Current (1)	I _{LI}	V _{IN} = V _{SS} to V _{CC} , #V _{CC} = V _{CC(MAX)}			WP/ACC: ±2.0 Others: ±1.0	μA
A9 Input Load Current	I _{LIT}	V _{CC} = to V _{CC(MAX)} ; A9 = 12.5V			35	μA
Output Leakage Current	I _{LO}	V _{OUT} = V _{SS} to V _{CC} , # V _{CC} = V _{CC(MAX)}			±1.0	μA
V _{CC} Active Current for Read (1)	I _{CC1}	CE# = V _{IL} #, OE# = V _{IH} , V _{CC} = V _{CC(MAX)} ; # f = 1 MHz, Byte Mode		24	80	mA
		CE# = V _{IL} #, OE# = V _{IH} , V _{CC} = V _{CC(MAX)} ; # f = 5MHz, Word Mode		120	200	mA
V _{CC} Intra-Page Read Current (1)	I _{CC2}	CE# = V _{IL} #, OE# = V _{IH} , V _{CC} = V _{CC(MAX)} ; f = 10MHz		1	10	mA
V _{CC} Active Erase/Program Current (2,3)	I _{CC3}	CE# = V _{IL} #, OE# = V _{IH} , V _{CC} = V _{CC(MAX)}		200	320	mA
V _{CC} Standby Current	I _{CC4}	V _{CC} = V _{CC(MAX)} ; V _{IO} = V _{CC} ; OE# = V _{IH} ; # V _{IL} = V _{SS} + 0.3V/-0.1V; # CE#, RESET# = V _{SS} ± 0.3V		4	20	μA
V _{CC} Reset Current	I _{CC5}	V _{CC} = V _{CC(MAX)} ; V _{IO} = V _{SS} + 0.3V/-0.1V; RESET# = V _{SS} ± 0.3V		4	20	μA
Automatic Sleep Mode (4)	I _{CC6}	V _{CC} = V _{CC(MAX)} ; V _{IO} = V _{CC} ; V _{IH} = V _{CC} ± 0.3V; #V _{IL} = V _{SS} + 0.3V/-0.1V; WP#/ACC = V _{IH}		4	20	μA
ACC Accelerated Program Current	I _{ACC}	CE# = V _{IL} , OE# = V _{IH} , V _{CC} = V _{CC(MAX)} , #WP#/ACC = V _{IH}	WP#/ACC pin	40	80	mA
			V _{CC} pin	200	320	
Input Low Voltage (5)	V _{IL}		-0.1		0.3 x V _{IO}	V
Input High Voltage (5)	V _{IH}		0.7 x V _{IO}		V _{IO} + 0.3	V
Voltage for ACC Erase/Program Acceleration	V _{HH}	V _{CC} = 2.7 - 3.6V	11.5		12.5	V
Voltage for Autoselect and Temporary Sector Unprotect	V _{ID}	V _{CC} = 2.7 - 3.6V	11.5		12.5	V
Output Low Voltage (5)	V _{OL}	I _{OL} = -100 μA			0.15 x V _{IO}	V
Output High Voltage (5)	V _{OH}	I _{OH} = -100 μA	0.85 x V _{IO}			V
Low V _{CC} Lock-Out Voltage	V _{LKO}		2.3		2.5	V

NOTES:

1. The I_{CC} current is typically less than 2 mA/MHz, with OE# at V_{IH}
2. I_{CC} active while Embedded Erase or Embedded Program or Write Buffer Programming is in progress.
3. Not 100% tested.
4. Automatic sleep mode enables the lower power mode when addresses remain stable for t_{ACC} + 30ns.
5. V_{IO} = 1.65-1.95V or 2.7-3.6V.
6. V_{CC} = 3 V and V_{IO} = 3V or 1.8V. When V_{IO} is at 1.8V, I/O pins cannot operate at 3V.

AC CHARACTERISTICS – WRITE/ERASE/PROGRAM OPERATIONS – WE# CONTROLLED $V_{CC} = 3.3V \pm 0.3V, -55^{\circ}C \leq T_A \leq +125^{\circ}C$

Parameter	Symbol		-100		-120		Unit
			Min	Max	Min	Max	
Write Cycle Time (3)	t _{AVAV}	t _{WC}	100		120		ns
Chip Select Setup Time (3)	t _{ELWL}	t _{CS}	0		0		ns
Write Enable Pulse Width	t _{WLWH}	t _{WP}	35		50		ns
Address Setup Time	t _{AVWL}	t _{AS}	0		0		ns
Data Setup Time	t _{DVWH}	t _{DS}	45		50		ns
Data Hold Time	t _{WHDX}	t _{DH}	0		0		ns
Address Hold Time	t _{WLAX}	t _{AH}	45		50		ns
Write Enable Pulse Width High (3)	t _{WHWL}	t _{WPH}	30		30		ns
Duration of Byte Programming Operation (1)	t _{WHWH1}			500		500	μs
Sector Erase (2)	t _{WHWH2}			3.5		5	sec
Read Recovery Time before Write (3)	t _{GHWL}		0		0		ns
VCC Setup Time	t _{VCS}		50		50		μs
Address Setup Time to OE# low during toggle bit polling		t _{ASO}	15		15		ns
Write Recovery Time from RY/BY# (3)		t _{RB}	0		0		ns
Program/Erase Valid to RY/BY#		t _{BUSY}	90		90		ns

NOTES:

1. Typical value for t_{WHWH1} is 60 μs.
2. Typical value for t_{WHWH2} is 0.5 sec.
3. Guaranteed by design, but not tested.

AC CHARACTERISTICS – READ-ONLY OPERATIONS $V_{CC} = 3.3V \pm 0.3V, -55^{\circ}C \leq T_A \leq +125^{\circ}C$

Parameter	Symbol		-100		-120		Unit
			Min	Max	Min	Max	
Read Cycle Time (1)	t _{AVAV}	t _{RC}	100		120		ns
Address Access Time	t _{AVQV}	t _{ACC}		100		120	ns
Chip Select Access Time	t _{ELQV}	t _{CE}		100		120	ns
Page Access Time		t _{PACC}		25		30	ns
Output Enable to Output Valid	t _{GLQV}	t _{OE}		25		35	ns
Chip Select High to Output High Z	t _{EHQZ}	t _{DF}		20		20	ns
Output Enable High to Output High Z	t _{GHQZ}	t _{DF}		20		20	ns
Output Hold from Addresses, CS# or OE# Change, Whichever occurs first	t _{AXQX}	t _{OH}	0		0		ns
Output Enable Hold Time (1)	Read	t _{OEH}	0		0		ns
	Toggle and Data# Polling		10		10		ns

1. Guaranteed by design, not tested.

FIGURE 2 – AC WAVEFORMS FOR READ OPERATIONS

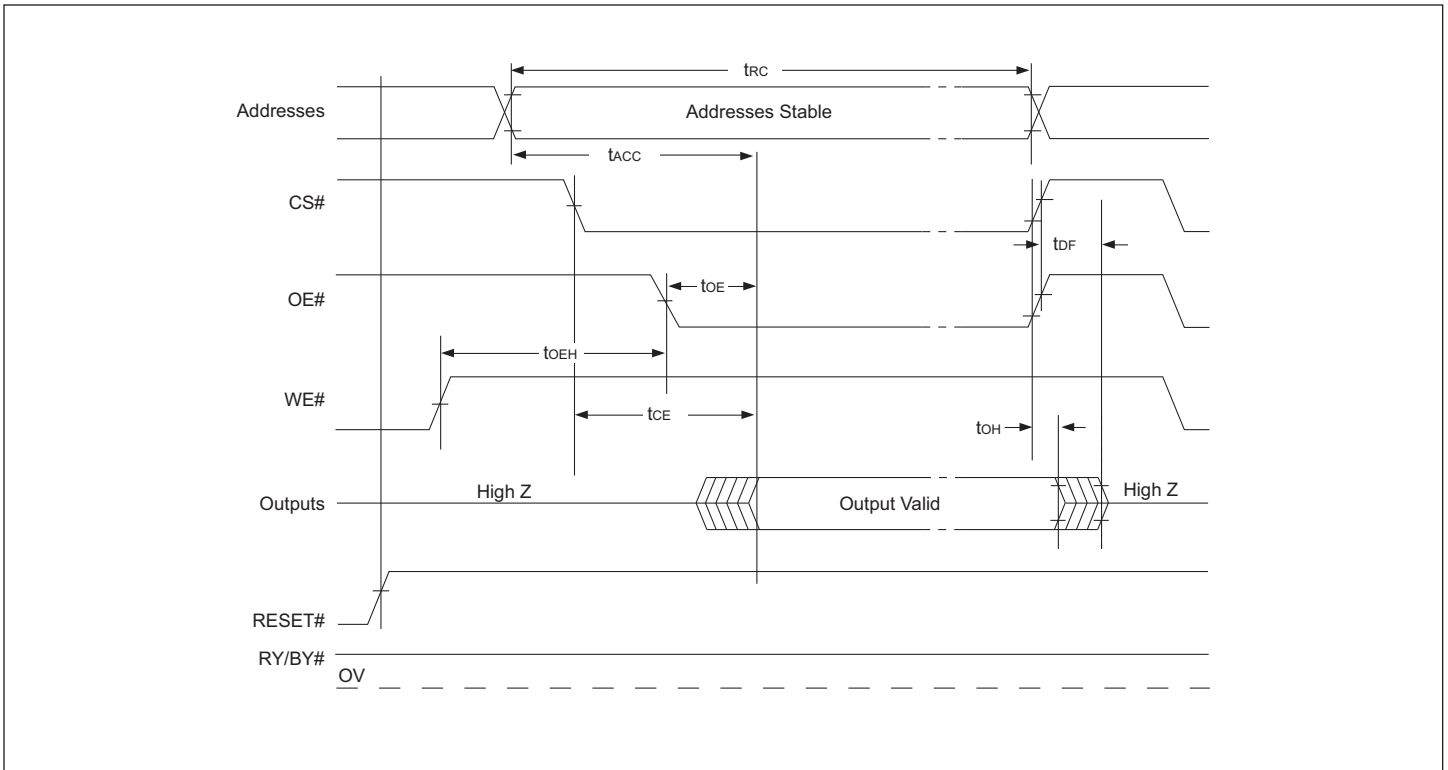
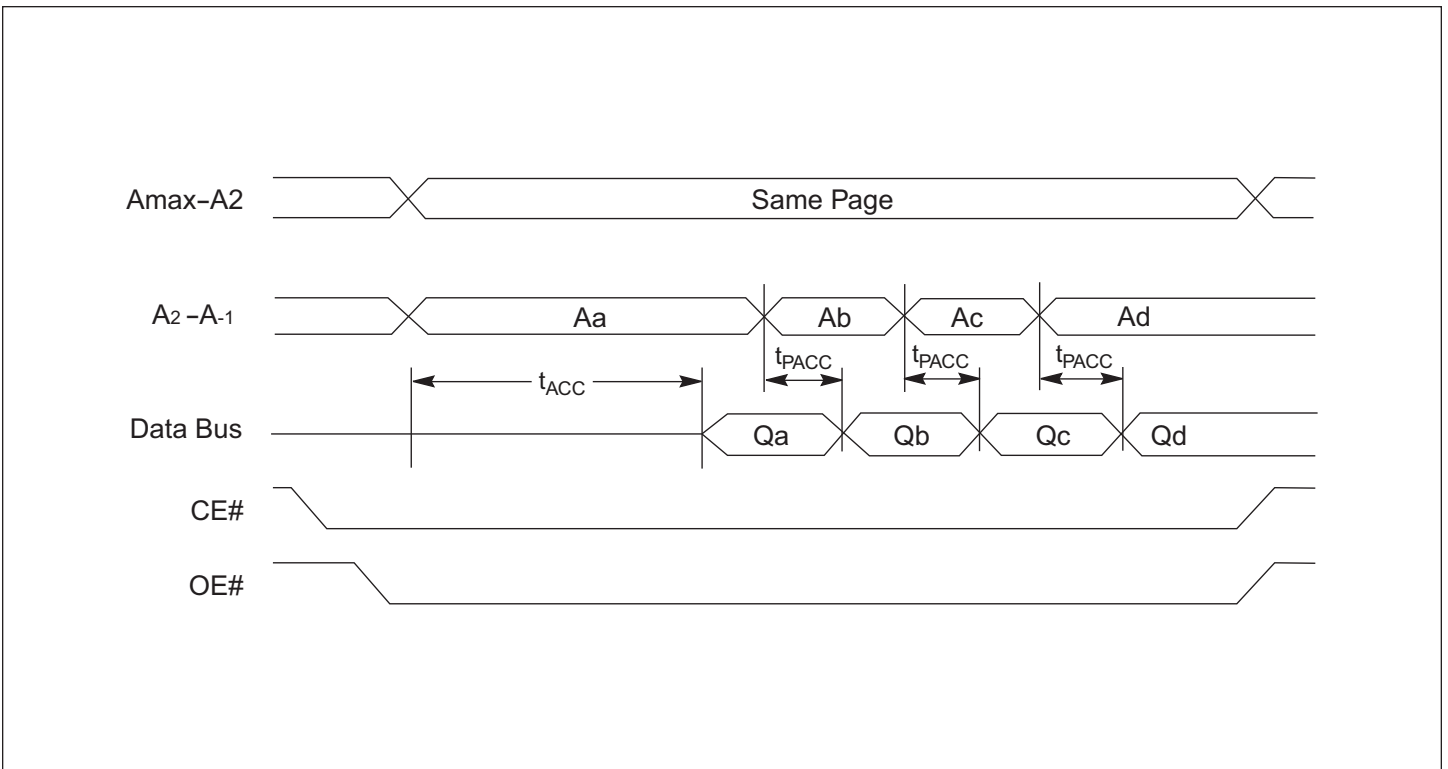


FIGURE 3 – PAGE READ TIMING



AC CHARACTERISTICS – HARDWARE RESET (RESET#)

Parameter	Symbol	Min	Max	Unit
RESET# Pin Low (During Embedded Algorithms) to Read Mode (1)	t_{ready}		20	μs
RESET# Pin Low (NOT During Embedded Algorithms) to Read Mode (1)	t_{ready}		500	ns
RESET# Pulse Width	t_{RP}	500		ns
RESET# High Time Before Read (1)	t_{RH}	50		ns
RESET# Low to Standby Mode (1)	t_{RPD}	20		μs
RY/BY# Recovery Time	t_{RB}	0		ns

NOTE: 1. Not tested.

FIGURE 4 – RESET TIMINGS NOT DURING EMBEDDED ALGORITHMS

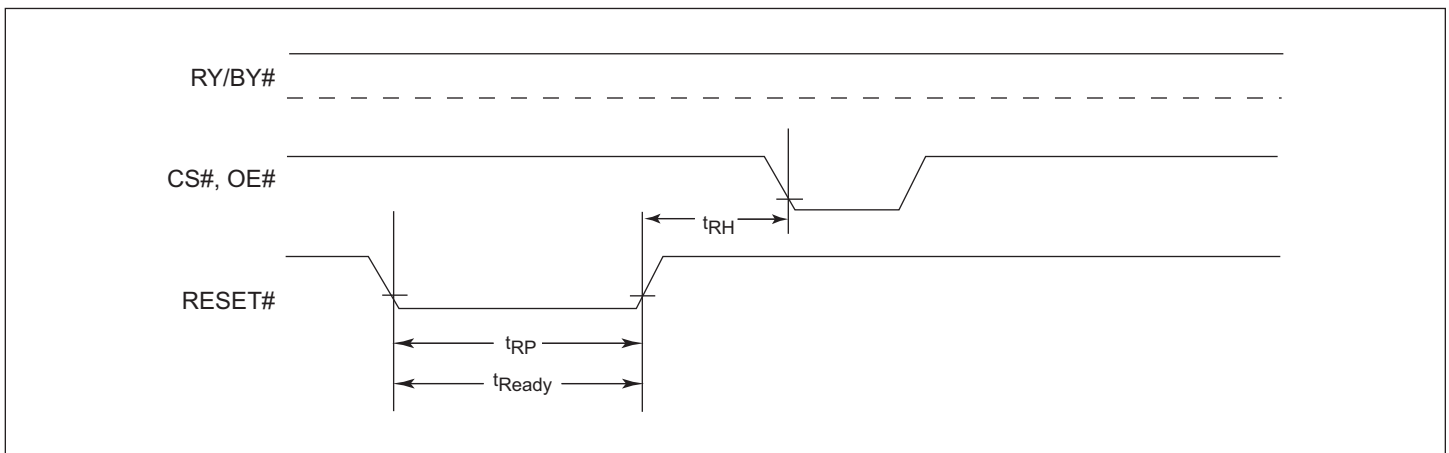


FIGURE 5: RESET TIMINGS DURING EMBEDDED ALGORITHMS

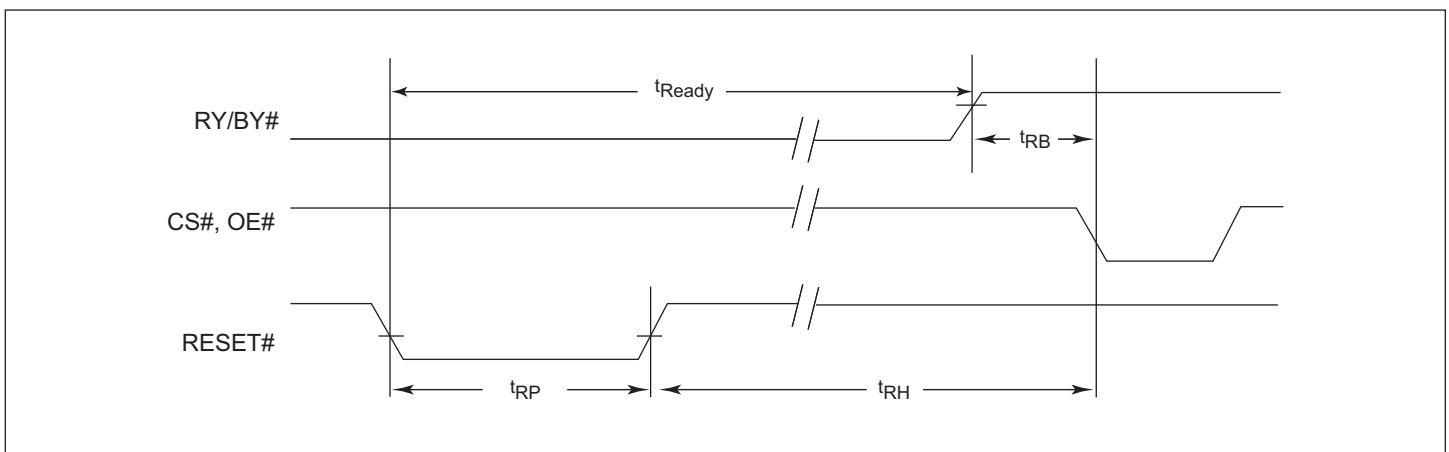
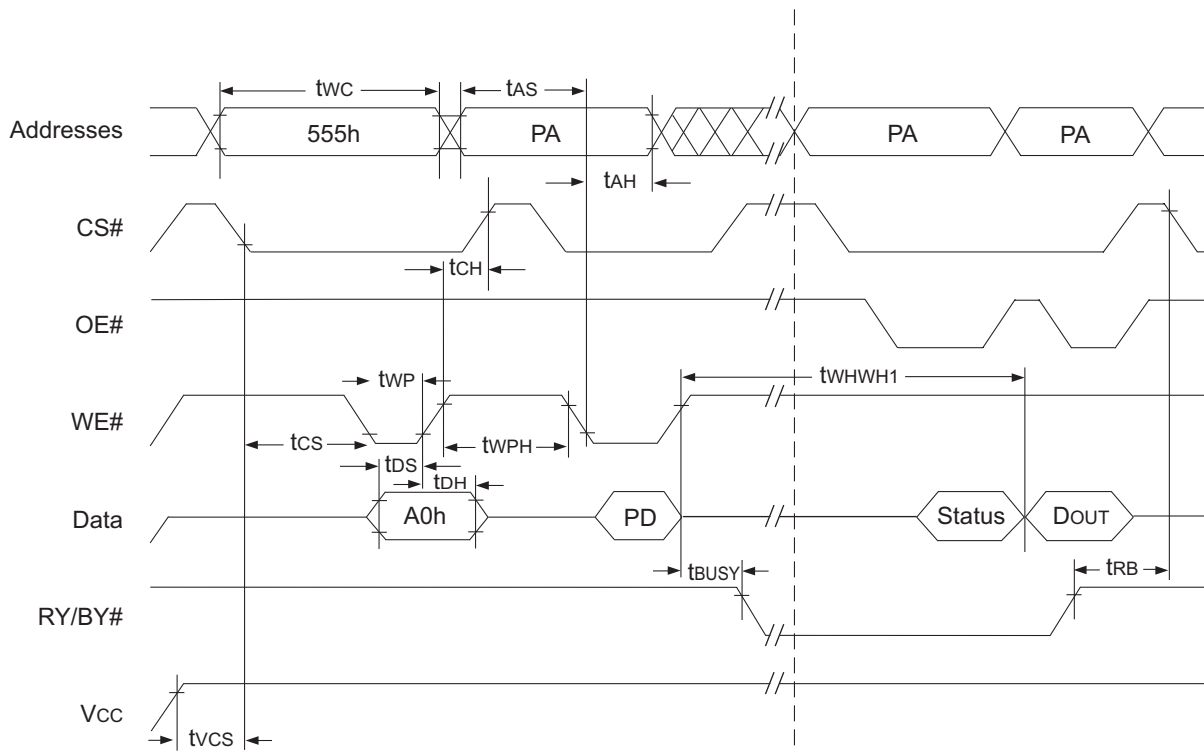


FIGURE 6 – PROGRAM OPERATIONS



NOTES:

1. PA is the address of the memory location to be programmed.
2. PD is the data to be programmed at byte address.
3. DOUT is the output of the data written to the device.
4. Figure indicates last two bus cycles of four bus cycle sequence.

FIGURE 7 – ACCELERATED PROGRAM TIMING DIAGRAM

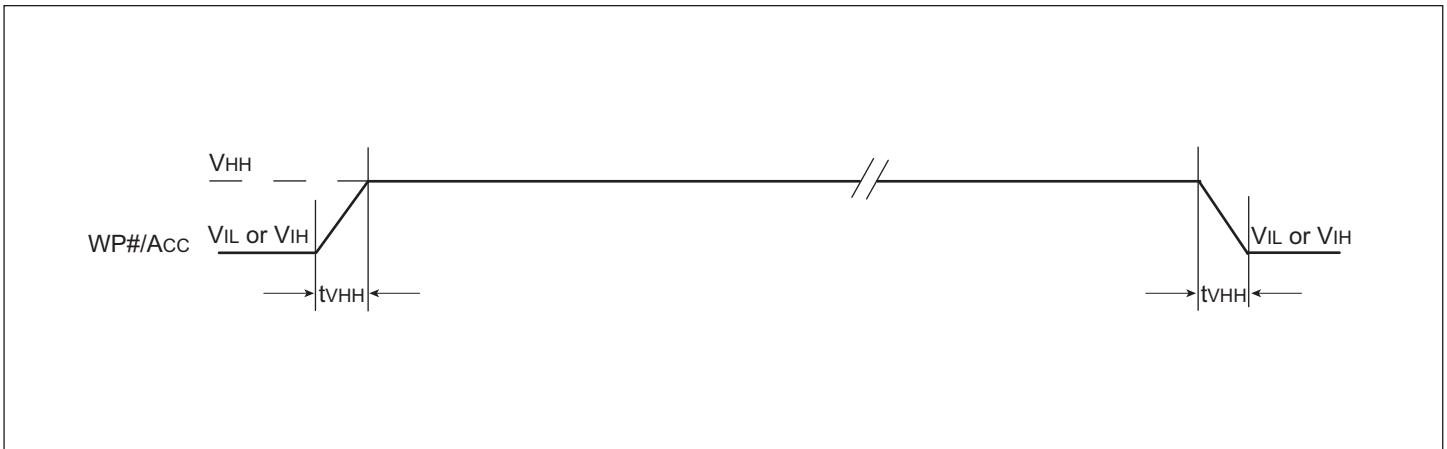
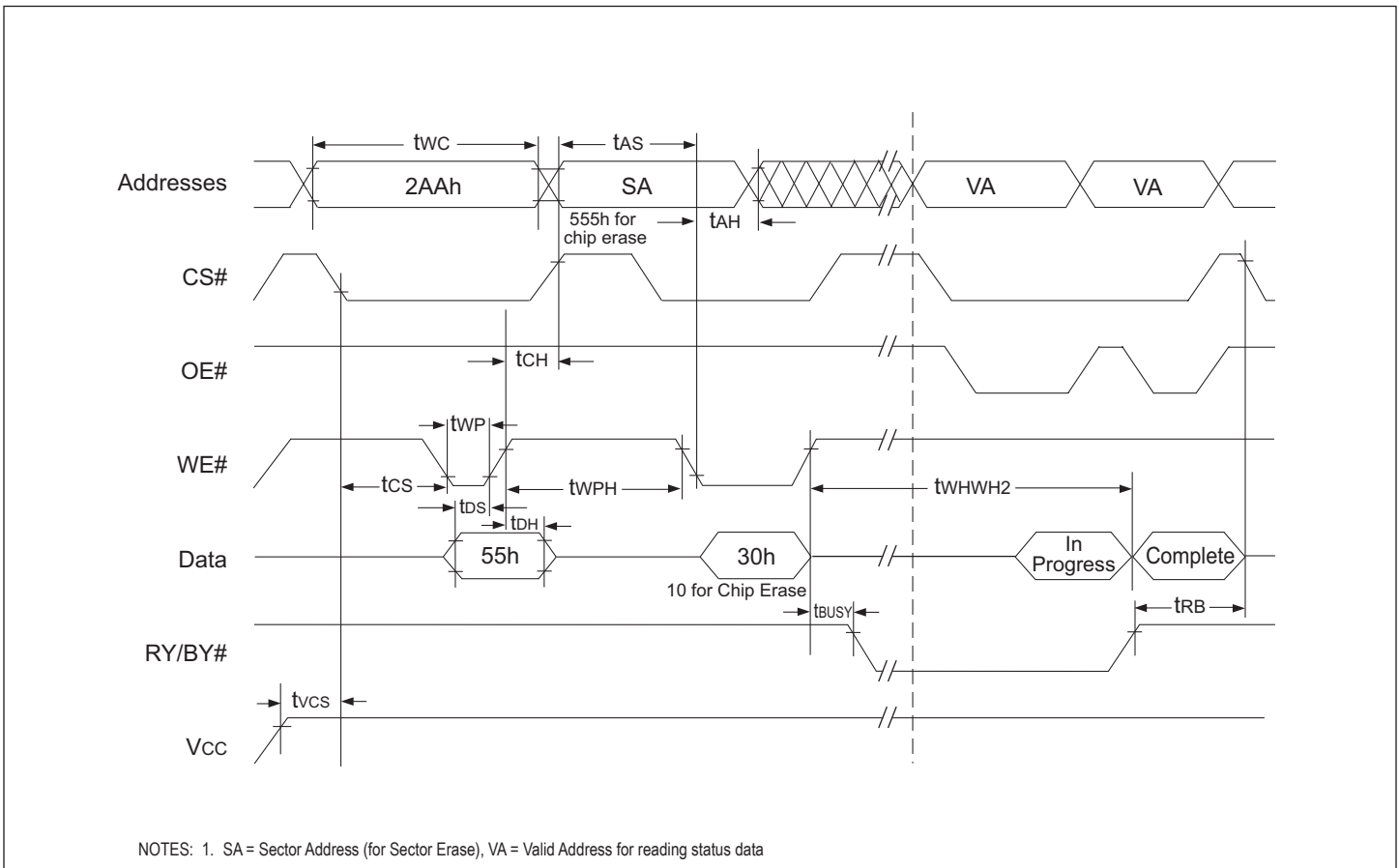
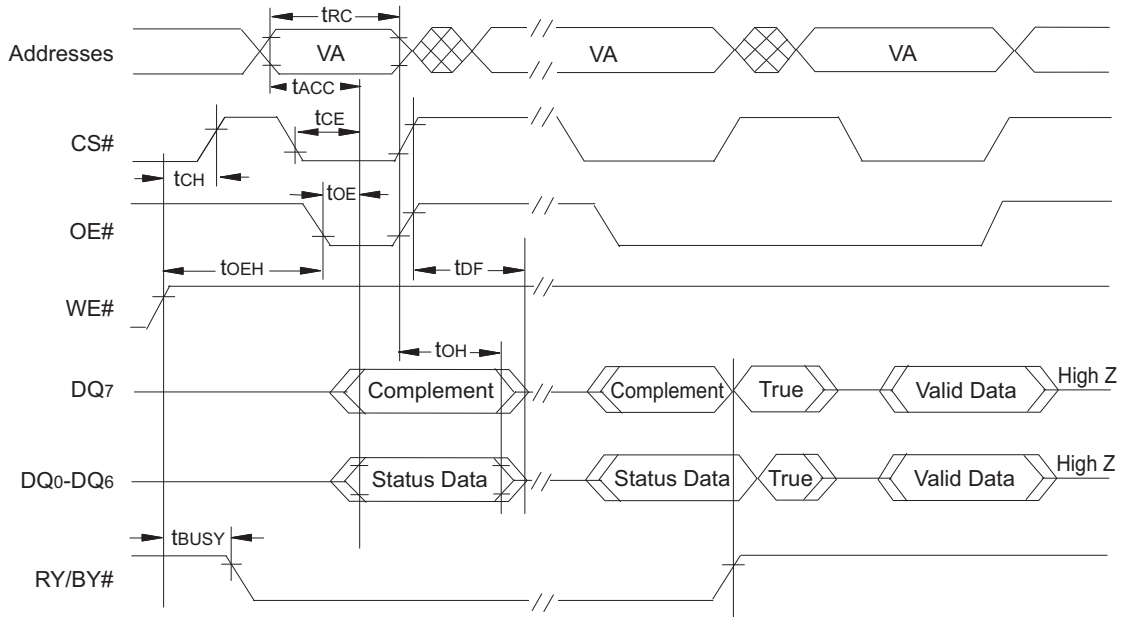


FIGURE 8: CHIP/SECTOR ERASE OPERATION TIMINGS



NOTES: 1. SA = Sector Address (for Sector Erase), VA = Valid Address for reading status data

FIGURE 9: DATA POLLING TIMINGS (DURING EMBEDDED ALGORITHMS)



NOTE: VA = Valid address. Illustration shows first status cycle after command sequence, last status read cycle, and array data read cycle.

FIGURE 10 – TOGGLE BIT TIMINGS (DURING EMBEDDED ALGORITHMS)

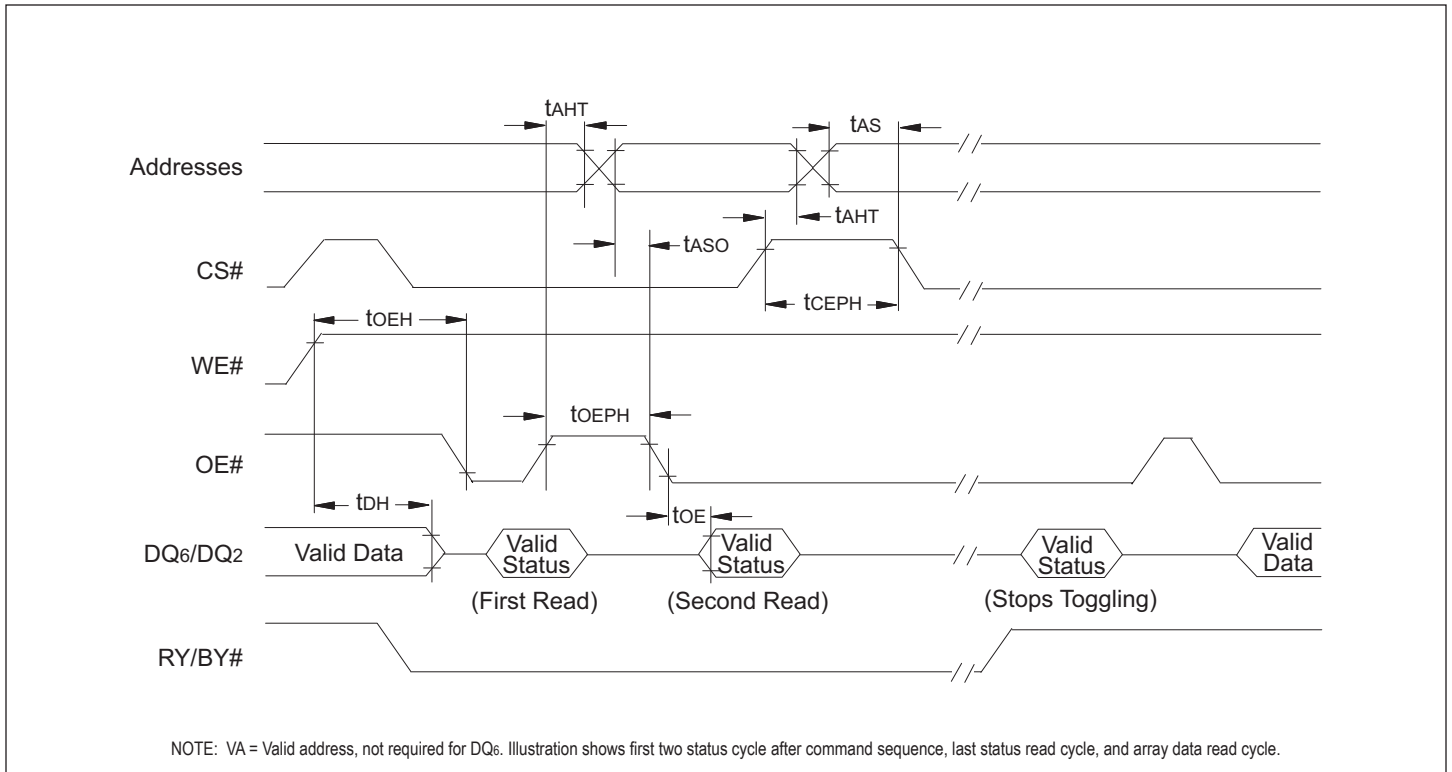
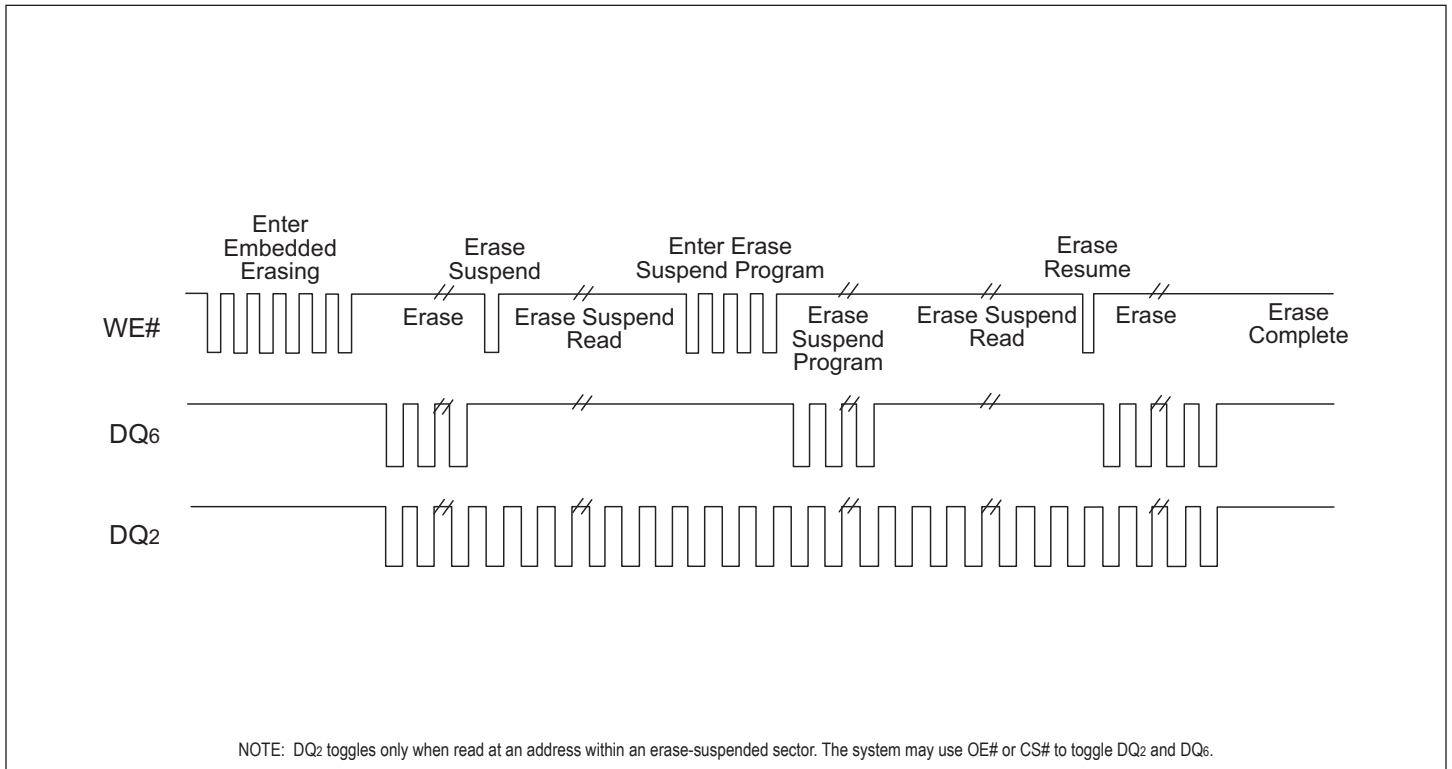


FIGURE 11 – DQ2 Vs. DQ6

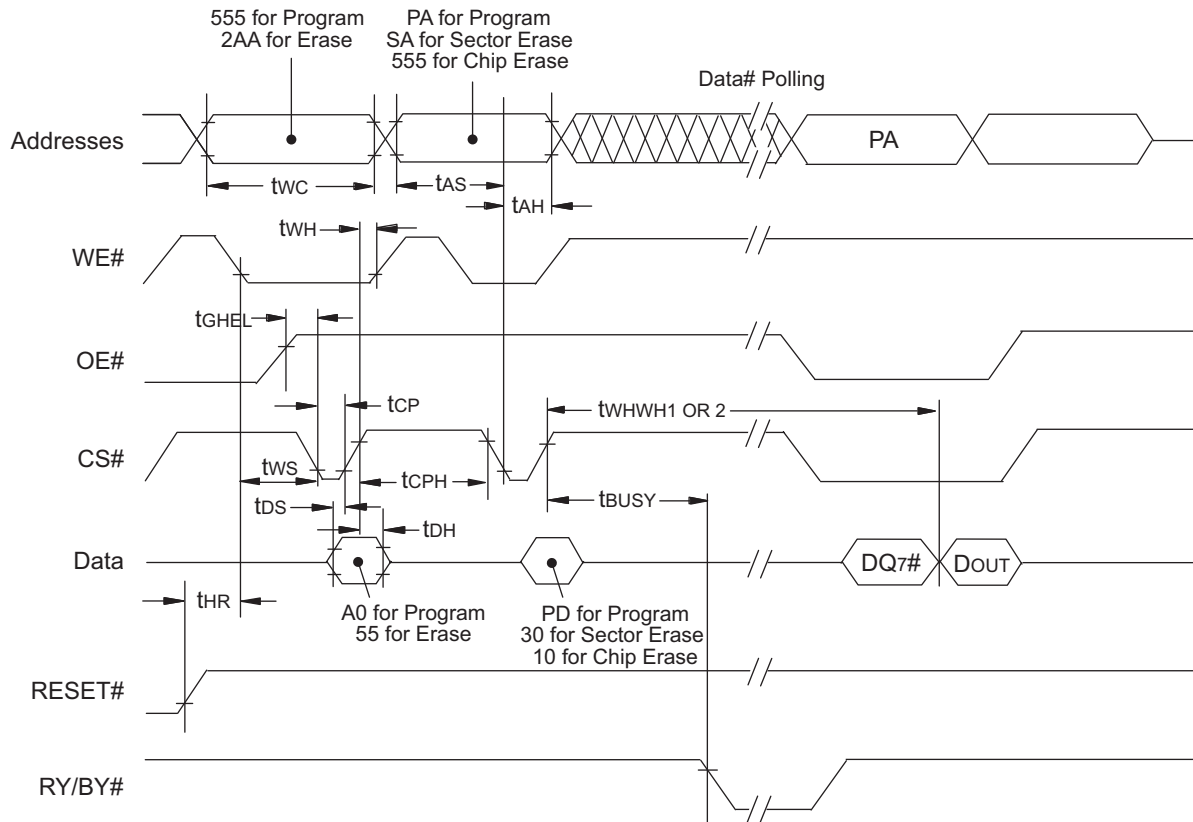


AC CHARACTERISTICS – ALTERNATE CS# CONTROLLED ERASE AND PROGRAM OPERATIONS

Parameter		Description		Speed Options		Unit
JEDEC	Std			100	120	
tAVAV	tWC	Write Cycle Time (1)	Min	100	120	ns
tAVWL	tAS	Address Setup Time	Min	0	0	ns
tELAX	tAH	Address Hold Time	Min	45	50	ns
tDVEH	tDS	Data Setup Time	Min	45	50	ns
tEHDx	tDH	Data Hold Time	Min	0	0	ns
tGHEL	tGHEL	Read Recovery Time Before Write (OE# High to WE# Low)	Min	0	0	ns
tWLEL	TWS	WE# Setup Time	Min	0	0	ns
tEHWH	tWH	WE# Hold Time	Min	0	0	ns
tELEH	tCP	CS# Pulse Width	Min	35	35	ns
tEHEL	tCPH	CS# Pulse Width High	Min	30	30	ns
tWHWH1	tWHWH1	Programming Operation	Typ	60	6	μs
tWHWH1	tWHWH1	Accelerated Programming Operation	Typ	54	54	μs
tWHWH2	tWHWH2	Sector Erase Operation	Typ	0.5	05	sec

NOTE: 1. Not tested.

FIGURE 12 – ALTERNATE CS# CONTROLLED WRITE (ERASE/PROGRAM) OPERATION TIMINGS

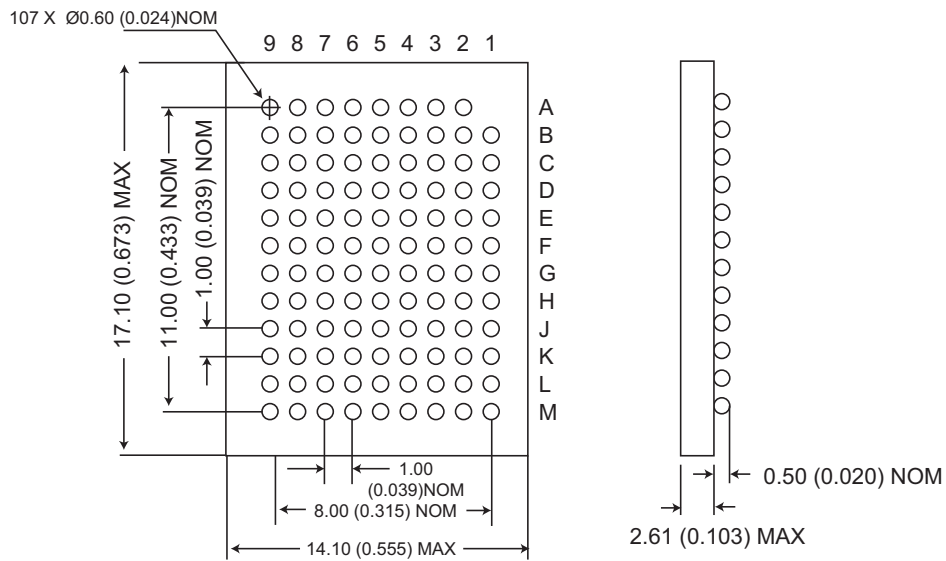


NOTES:

1. Figure indicates last two bus cycles of a program or erase operation.
2. PA = program address, SA = sector address, PD = program data.
3. DQ7 is the complement of the data written to the device. DOUT is the data written to the device.

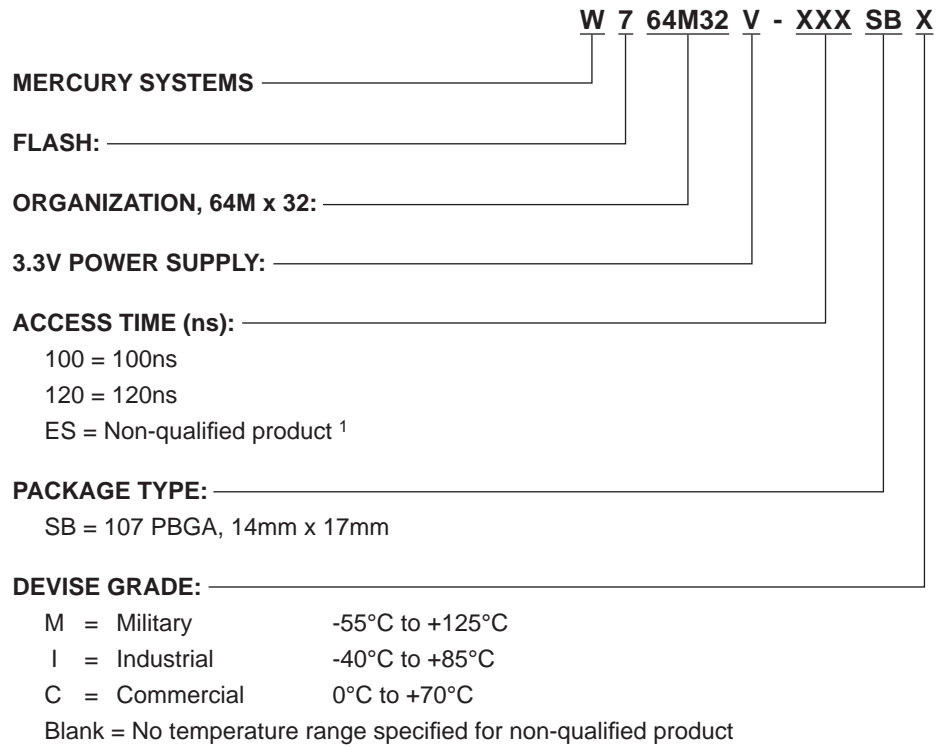
PACKAGE 107 – PBGA (PLASTIC BALL GRID ARRAY)

BOTTOM VIEW



ALL LINEAR DIMENSIONS ARE IN MILLIMETERS AND PARENTHETICALLY IN INCHES

ORDERING INFORMATION



NOTE 1: W764M32V-ESSB is only available product until completion of qualification.

Document Title

64Mx32 NOR Flash Multi-Chip Package 3.0V Page Mode Flash Memory

Revision History

Rev #	History	Release Date	Status
Rev 0	Initial Release	November 2005	Advanced
Rev 1	Changes (All Pages) 1.1 Add AC + DC characteristics and timing diagrams 1.2 Update package dimensions 1.3 Add preliminary pinout	February 2006	Advanced
Rev 2	Changes (Pg. 1, 3, 16) 2.1 Correct typographical error in pinout on page 3, ball 'B4' is DQ9	March 2006	Advanced
Rev 3	Changes (Pg. 1, 2, 16) 3.1 Change status to Preliminary 3.2 Remove reference to BYTE# input and 64-bit data bus. These options are not available 3.3 Add capacitance values to table	January 2007	Preliminary
Rev 4	Changes (Pg. 4) 4.1 Change status to Final	May 2007	Final
Rev 5	Changes (All Pages) 5.1 Remove "Endurance (write/erase cycles); 1,000,000; cycle from absolute maximum ratings	March 2009	Final
Rev 6	Changes (All Pages) 6.1 Change dimension from 2.32 (0.091) MAX to 2.61 (0.103) MAX	March 2009	Final
Rev 7	Changes (All Pages) 7.1 Change document layout from White Electronic Designs to Microsemi	June 2011	Final
Rev 8	Changes (1, 16) 8.1 Add "NOR" to headline	August 2011	Final
Rev 9	Changes (3) 9.1 Add BGA Thermal Resistance table	January 2012	Final
Rev 10	Changes (1-16) 10.1 Added "Not Recommended for New Designs — Replaced by W764M32V1-XBX"	June 2012	Final
Rev 11	Changes (Pg. All) (ECN 10156) 11.1 Change document layout from Microsemi to Mercury Systems	September 2016	Final

